

P-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (mΩ)(Typ.)	I _D (A) ^a	Q _g (Typ.)			
-40	3 at V _{GS} = - 10 V	400	80 nC			
-40	4 at V _{GS} = - 4.5 V	-130				

FEATURES

- DT-Trench Power MOSFET
- · Low Gate Charge
- \bullet 100 % R $_{\rm g}$ and UIS Tested
- AEC-Q101 Qualified for Automotive Applications

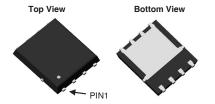


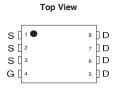
RoHS

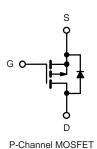
APPLICATIONS

- · PWM Applications
- Load Switch
- Power Management

DFN5X6-8L Pin Configuration







ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V_{DS}	- 40	.,,			
Gate-Source Voltage	V _{GS}	± 20	V			
Continuous Drain Current	T _C = 25 °C	1	- 130			
Continuous Drain Current	T _C = 100 °C	I _D	- 98			
Continuous Source Current (Diode Conduction)	I _S	- 125	А			
Pulsed Drain Current ^a	I _{DM}	- 520				
Single Pulse Avalanche Current		I _{AS}	- 120			
Single Pulse Avalanche Energy L = 0.1 mH		E _{AS}	150	mJ		
Maximum Power Dissipation ^b	T _C = 25 °C	D	90	W		
waximum rower bissipation	T _C = 100 °C	P_{D}	43			
Operating Junction and Storage Temperature R	T _J , T _{stg}	- 55 to + 175	°C			

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Case (Drain) ^{C,d}	RthJC	1.39	°C/W		

Notes:

- a. BasedonTC= 25°C.
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



Parameter	Symbol	Test Conditions	Min .	Тур.	Max.	Unit	
Static				•			
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$				V	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-1		-3	V	
Gate-Source Leakage	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$				± 100	nA	
Zara Cata Valtaga Brain Current		V _{DS} = -40 V, V _{GS} = 0 V			-1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -30 V, V _{GS} = 0 V, T _J = 125 °C		-20		μA	
D : 0	D	V _{GS} = - 10 V, I _D = - 20 A		3	3.8	3.8 5.5	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 20 A		4	5.5		
Forward Transconductance ^a	9 _{fs}	V _{DS} = -10 V,I _D = - 20 A		40		S	
Dynamic ^b					<u> </u>		
Input Capacitance	C _{iss}			10400		pF	
Output Capacitance	C _{oss}	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		818			
Reverse Transfer Capacitance	C _{rss}			961			
Total Gate Charge	Q_g			80			
Gate-Source Charge	Q_{gs}	$V_{DS} = -20 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -20 \text{ A}$		12		nC	
Gate-Drain Charge	Q_{gd}			7.5			
Gate Resistance	R_{g}	f = 1 MHz		1.5		Ω	
Turn-On Delay Time	t _{d(on)}			15			
Rise Time	t _r	V_{DS} = -20 V, R_L = 4 Ω		90			
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -20 \text{A}, V_{GS} = -10 \text{V}, R_g = 6 \Omega$		110		ns	
Fall Time	t _f			85			
Drain-Source Body Diode Characteristics	3						
Continuous Source-Drain Diode Current	I _S	T _A = 25 °C			- 130	Α	
Pulse Diode Forward Current ^a	I _{SM}				- 520		
Body Diode Voltage	V_{SD}	I _S = - 1 A			- 1.2	V	
Body Diode Reverse Recovery Time		1 20 A di/dt 100 A/vo T 25 °C		30		ns	
Body Diode Reverse Recovery Charge	Q _{rr}	$I_F = -20 \text{ A, di/dt} = 100 \text{ A/}\mu\text{s, T}_J = 25 \text{ °C}$		20		nC	

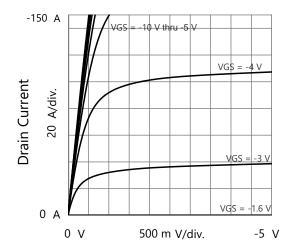
Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

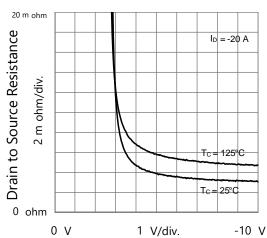
a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

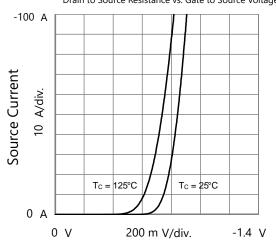
TYPICAL CHARACTERISTICS (25 C, unless otherwise noted)



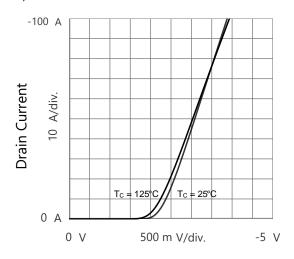
Drain to Source Voltage Output Characteristics



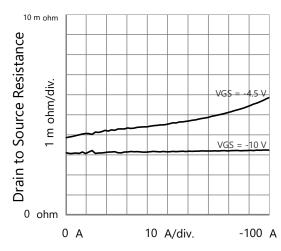
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



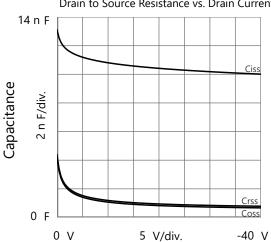
Source to Drain Voltage Body Diode Forward Characteristics



Gate to Source Voltage Transfer Characteristics



Drain Current
Drain to Source Resistance vs. Drain Current



Drain to Source Voltage Capacitances



TYPICAL CHARACTERISTICS (25 C, unless otherwise noted)

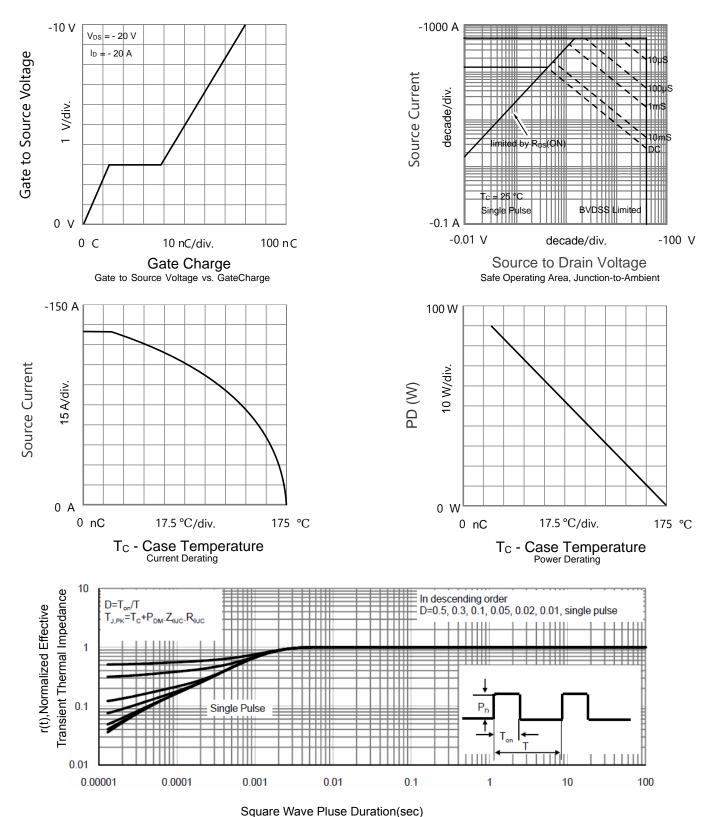
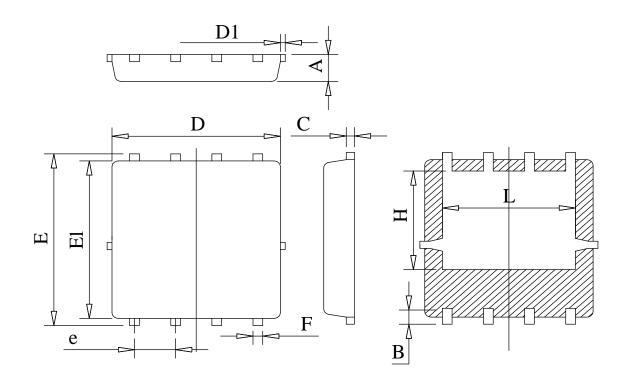


Figure 13 Normalized Maximum Transient Thermal Impedance



DFN5X6-8L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Unit: mm

Symbol	Min	Тур	Max
A	0.78	0.95	1.12
В	0.45	0.58	0.78
С	0.18	0.254	0.36
D	4.70	5.20	5.45
D1			0.18
Е	5.85	6.05	6.25
E1	5.38	5.55	5.98
e	1.15	1.27	1.40
F	0.18	0.30	0.52
Н	3.25	3.47	3.70
L	3.75	4.00	4.25





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